

Supplementary Materials: Improving the Thermoelectric Properties of the Half-Heusler Compound VCoSb by Vanadium Vacancy

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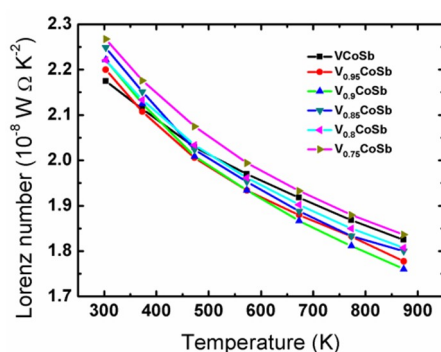


Figure S1. The Lorentz number estimated by fitting the Seebeck coefficient.

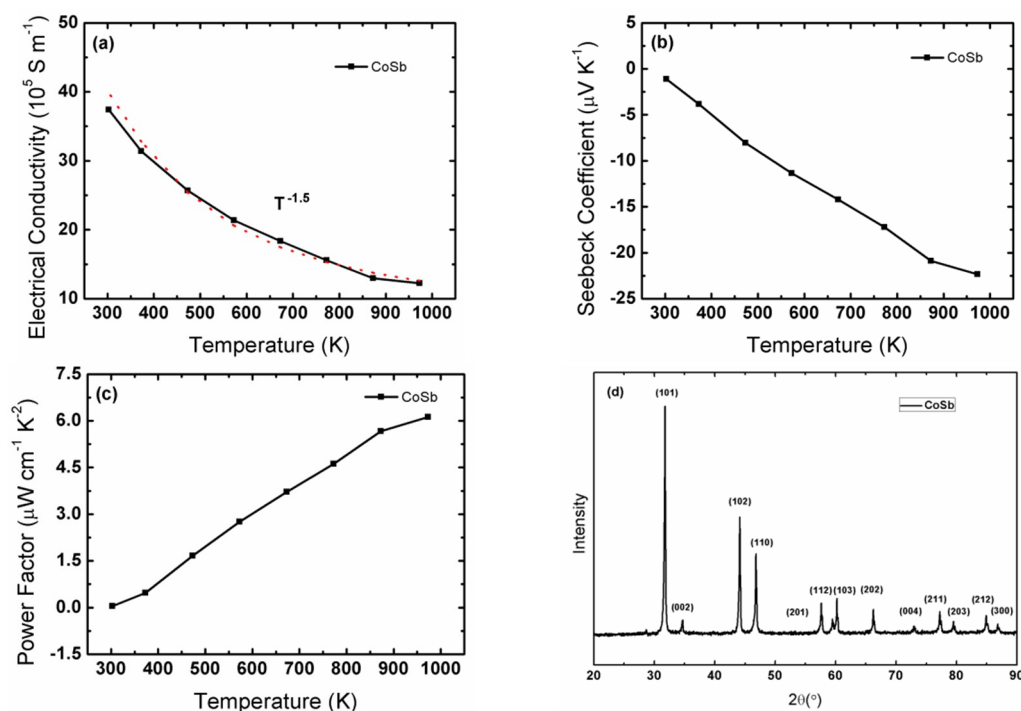


Figure S2. Temperature-dependent electrical conductivity (a), Seebeck coefficient (b), power factor (c), and XRD pattern (d) of CoSb.